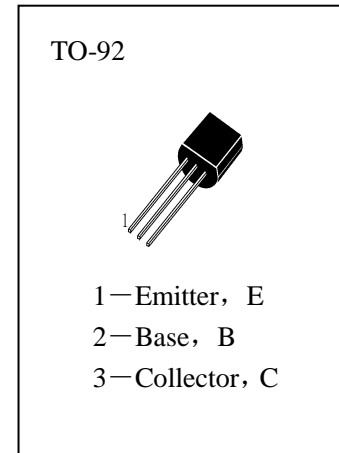


■ APPLICATIONS

The H945 is designed for driver stage of AF amplifier
And low speed switching.

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	Storage Temperature	-55~150°C
T _j	Junction Temperature	150°C
P _C	Collector Dissipation	250mW
V _{CB0}	Collector-Base Voltage	60V
V _{CEO}	Collector-Emitter Voltage	50V
V _{EBO}	Emitter-Base Voltage	5V
I _C	Collector Current	150mA



■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CB0}	Collector-Base Breakdown Voltage	60			V	I _C =100 μA, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	50			V	I _C =100 μA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	5			V	I _E =100 μA, I _C =0
h _{FE}	DC Current Gain	90		600		V _{CE} =6V, I _C =1mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage			0.3	V	I _C =100mA, I _B =10mA
V _{BE(sat)}	Base-Emitter Saturation Voltage			1.0	V	I _C =100mA, I _B =10mA
I _{CBO}	Collector Cut-off Current			100	nA	V _{CB} =60V, I _E =0
I _{EBO}	Emitter Cut-off Current			100	nA	V _{EB} =5V, I _C =0
f _T	Current Gain-Bandwidth Product		250		MHz	V _{CE} =6V, I _C =10mA
C _{ob}	Output Capacitance		3.0		pF	V _{CB} =6V, I _E =0, f=1MHz
NF	Noise Figure		4.0		dB	V _{CE} =6V, I _C =0.5mA, f=1KHz, R _S =500 Ω

■ h_{FE} Classification

R	Q	P	K
90—180	135—270	200—400	300—600

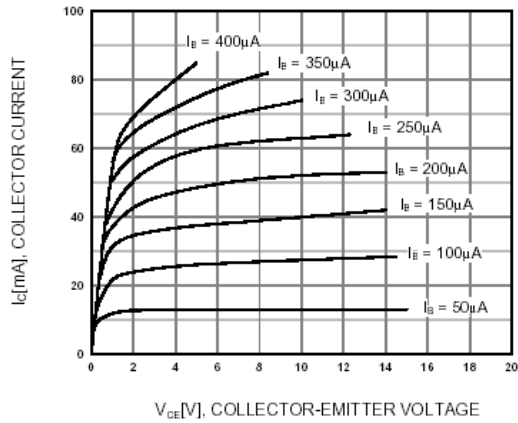


Figure 1. Static Characteristic

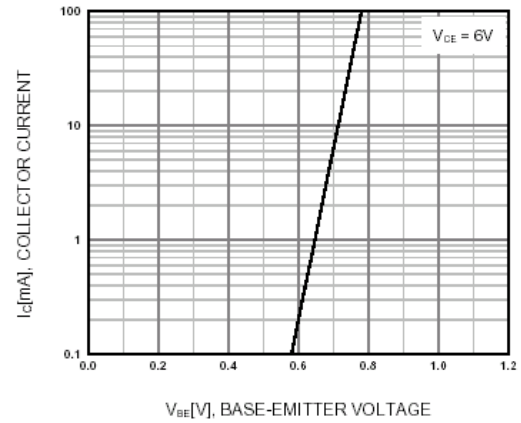


Figure 2. Transfer Characteristic

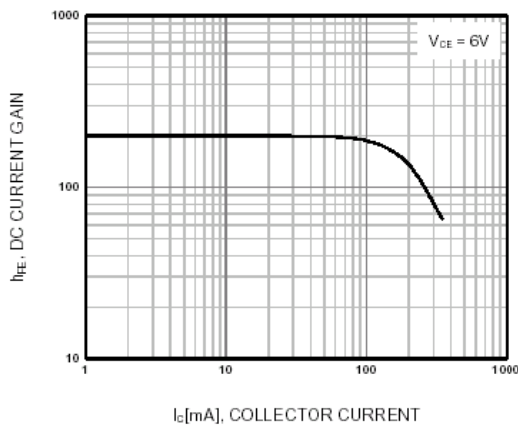


Figure 3. DC current Gain

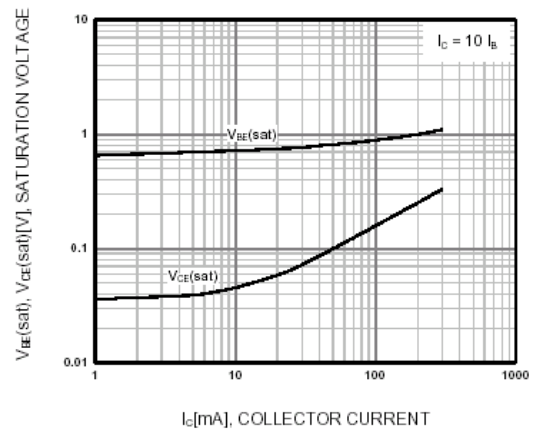


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

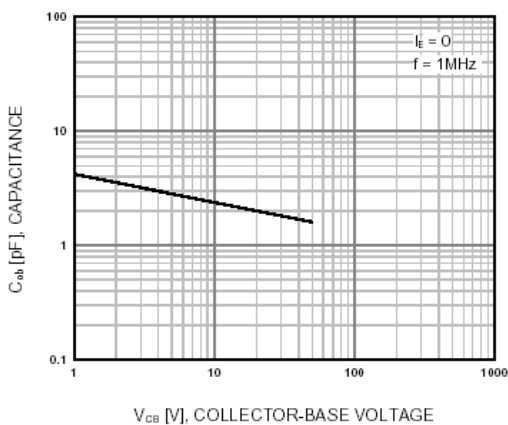


Figure 5. Output Capacitance

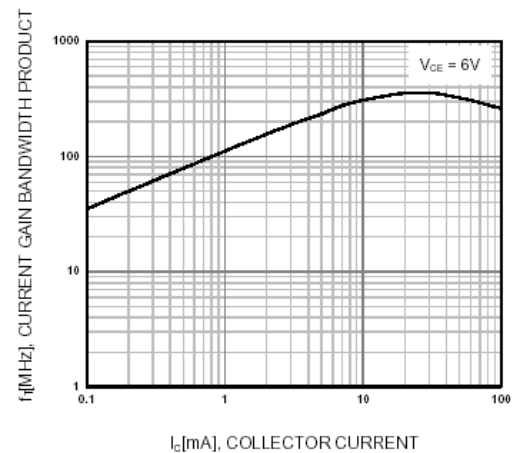


Figure 6. Current Gain Bandwidth Product